

BC636/638/640

Switching and Amplifier Applications

• Complement to BC635/637/639



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings Ta=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|---|-----------|-------|
| V _{CER} | Collector-Emitter Voltage at R _{BE} =1KΩ | | |
| | : BC636 | -45 | V |
| | : BC638 | -60 | V |
| | : BC640 | -100 | V |
| V _{CES} | Collector-Emitter Voltage | | |
| : BC636 | : BC636 | -45 | V |
| | : BC638 | -60 | V |
| | : BC640 | -100 | V |
| V _{CEO} | Collector-Emitter Voltage | | |
| | : BC636 | -45 | V |
| | : BC638 | -60 | V |
| | : BC640 | -80 | V |
| V _{EBO} | Emitter-Base Voltage | -5 | V |
| I _C | Collector Current | -1 | Α |
| I _{CP} | Peak Collector Current | -1.5 | А |
| I _B | Base Current | -100 | mA |
| P _C | Collector Dissipation | 1 | W |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -65 ~ 150 | °C |

Electrical Characteristics T_a =25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|---|------|------|------|-------|
| BV _{CEO} | Collector-Emitter Breakdown Voltage | I _C = -10mA, I _B =0 | | | | |
| | : BC636 | | -45 | | | V |
| | : BC638 | | -60 | | | V |
| | : BC640 | | -80 | | | V |
| I _{CBO} | Collector Cut-off Current | V _{CB} = -30V, I _E =0 | | | -0.1 | μΑ |
| I _{EBO} | Emitter Cut-off Current | V_{EB} = -5V, I_{C} =0 | | | -0.1 | μΑ |
| h _{FE1} | DC Current Gain : All | V_{CE} = -2V, I_{C} = -5mA | 25 | | | |
| h_{FE2} | : BC636 | $V_{CE} = -2V, I_{C} = -150 \text{mA}$ | 40 | | 250 | |
| | : BC638/BC640 | | 40 | | 160 | |
| h_{FE3} | : All | $V_{CE} = -2V, I_{C} = -500 \text{mA}$ | 25 | | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = -500mA, I _B = -50mA | | | -0.5 | V |
| V _{BE} (on) | Base-Emitter On Voltage | V _{CE} = -2V, I _C = -500mA | | | -1 | V |
| f _T | Current Gain Bandwidth Product | V_{CE} = -5V, I_{C} = -10mA, f=50MHz | | 100 | | MHz |

Typical Characteristics

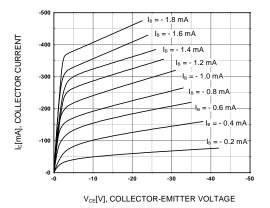


Figure 1. Static Characteristic

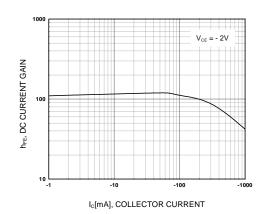


Figure 2. DC current Gain

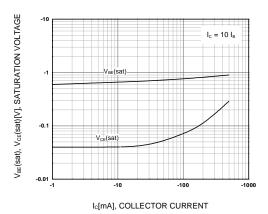


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

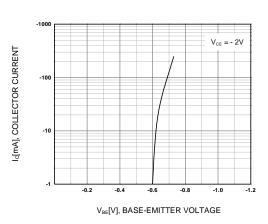


Figure 4. Base-Emitter On Voltage

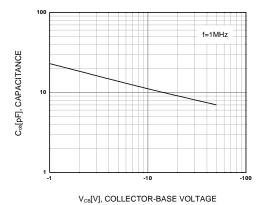
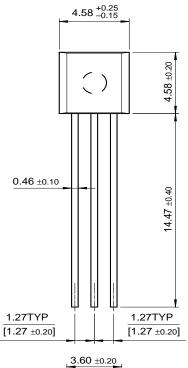
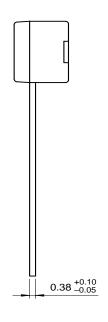


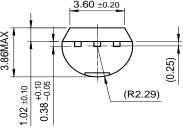
Figure 5. Collector Output Capacitance

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Dimensions in Millimeters

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